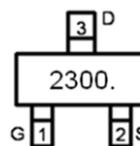
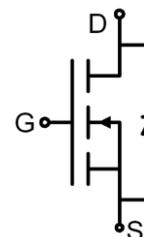


Main Product Characteristics:

V_{DSS}	20V
$R_{DS(on)}$	22m Ω (typ.)
I_D	3.3A


SOT-23

Marking and Pin Assignments

Schematic Diagram
Features and Benefits

- Advanced MOSFET process technology
- Special designed for PWM, load switching and general purpose applications
- Ultra low on-resistance with low gate charge
- Fast switching and reverse body recovery
- 150°C operating temperature


Description:

It utilizes the latest processing techniques to achieve the high cell density and reduces the on-resistance with high repetitive avalanche rating. These features combine to make this design an extremely efficient and reliable device for use in power switching application and a wide variety of other applications.

Absolute Max Rating:

Symbol	Parameter	Max.	Units
$I_D @ T_C = 25^\circ\text{C}$	Continuous Drain Current, $V_{GS} @ 10\text{V}$ ①	3.3	A
I_{DM}	Pulsed Drain Current②	11.4	
$P_D @ T_C = 25^\circ\text{C}$	Power Dissipation③	1.1	W
V_{DS}	Drain-Source Voltage	20	V
V_{GS}	Gate-to-Source Voltage	± 12	V
$T_J \quad T_{STG}$	Operating Junction and Storage Temperature Range	-55 to +150	$^\circ\text{C}$

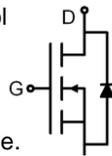
Thermal Resistance

Symbol	Characterizes	Typ.	Max.	Units
R _{θJA}	Junction-to-Ambient ^④	—	140	°C/W

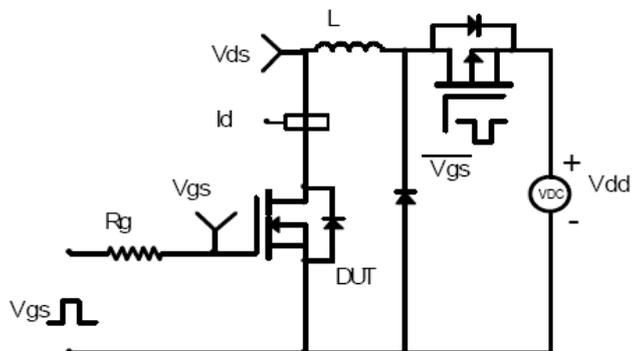
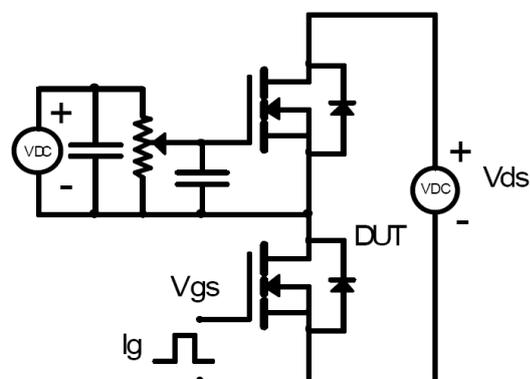
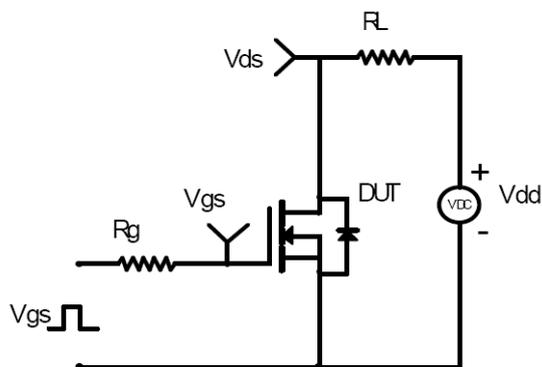
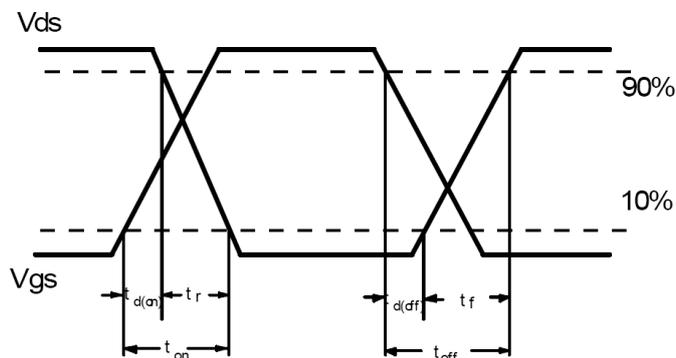
Electrical Characterizes @T_A=25°C unless otherwise specified

Symbol	Parameter	Min.	Typ.	Max.	Units	Conditions
V _{(BR)DSS}	Drain-to-Source breakdown voltage	20	—	—	V	V _{GS} = 0V, I _D = 250μA
R _{DS(on)}	Static Drain-to-Source on-resistance	—	22	30	mΩ	V _{GS} =4.5V, I _D =2A
		—	27	40	mΩ	V _{GS} =2.5V, I _D =1A
V _{GS(th)}	Gate threshold voltage	0.4	—	1	V	V _{DS} = V _{GS} , I _D =250μA
I _{DSS}	Drain-to-Source leakage current	—	—	1	μA	V _{DS} =20V, V _{GS} = 0V
I _{GSS}	Gate-to-Source forward leakage	—	—	100	nA	V _{GS} =12V
		—	—	-100		V _{GS} = -12V
Q _g	Total gate charge	—	4.0	—	nC	I _D = 3.6A, V _{DS} =10V, V _{GS} = 4.5V
Q _{gs}	Gate-to-Source charge	—	0.65	—		
Q _{gd}	Gate-to-Drain("Miller") charge	—	1.5	—		
t _{d(on)}	Turn-on delay time	—	7	—	ns	V _{GS} =4.5V, V _{DD} =20V, R _{GEN} =3Ω R _L =10Ω
t _r	Rise time	—	10.4	—		
t _{d(off)}	Turn-Off delay time	—	12.9	—		
t _f	Fall time	—	3.2	—		
C _{iss}	Input capacitance	—	304	—	pF	V _{GS} = 0V V _{DS} = 20V f = 1MHz
C _{oss}	Output capacitance	—	46	—		
C _{riss}	Reverse transfer capacitance	—	38	—		

Source-Drain Ratings and Characteristics

Symbol	Parameter	Min.	Typ.	Max.	Units	Conditions
I _S	Continuous Source Current (Body Diode)	—	—	3.3	A	MOSFET symbol showing the integral reverse p-n junction diode. 
I _{SM}	Pulsed Source Current (Body Diode)	—	—	11.4	A	
V _{SD}	Diode Forward Voltage	—	0.7	1.2	V	I _S =1A, V _{GS} =0V

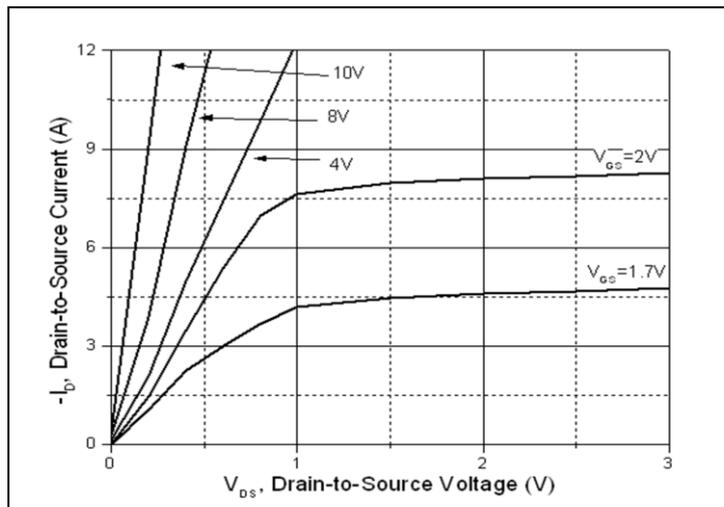
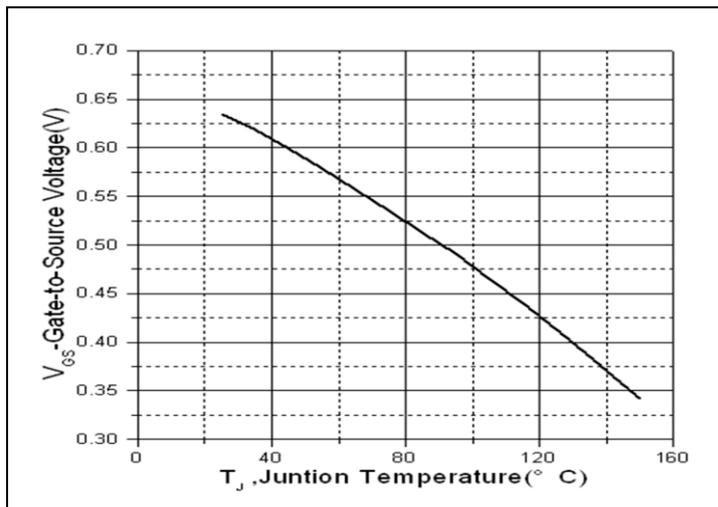
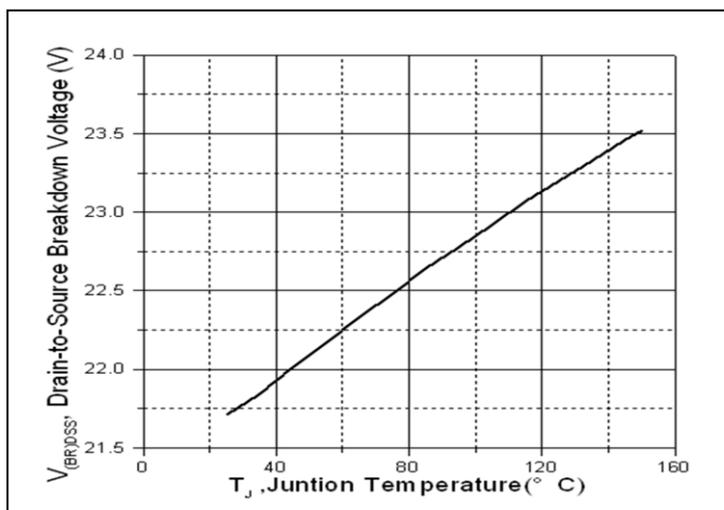
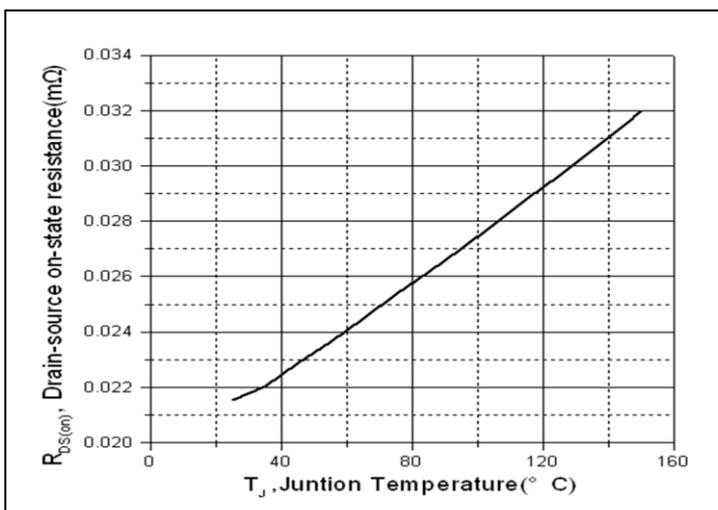
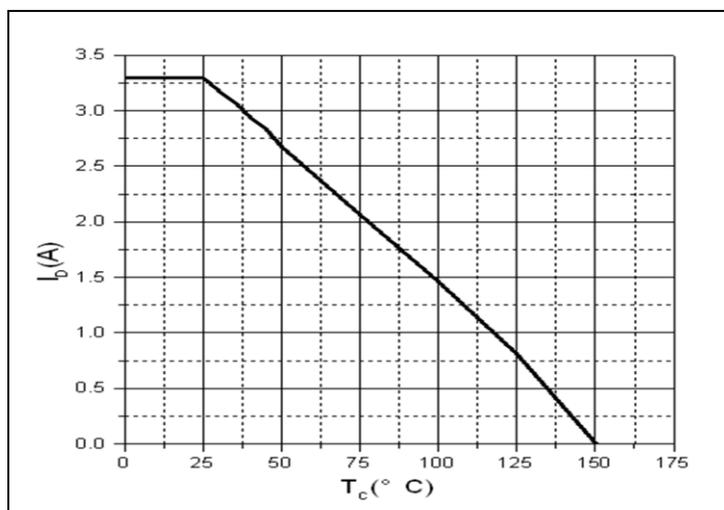
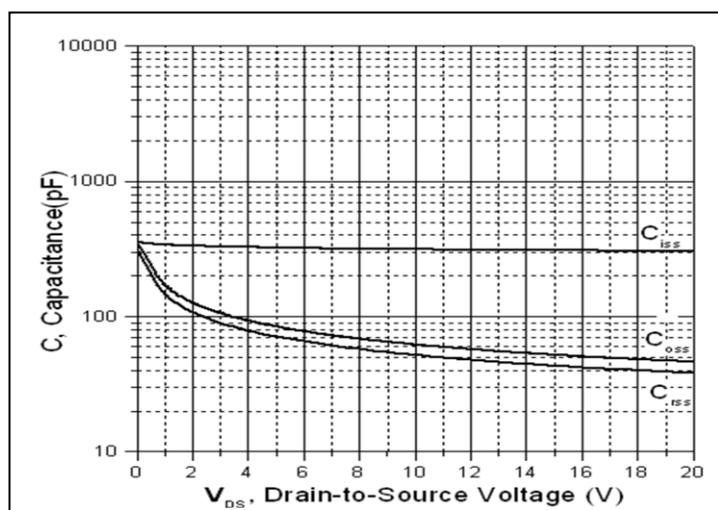
Test Circuits and Waveforms

EAS Test Circuit:

Gate Charge Test Circuit:

Switching Time Test Circuit:

Switching Waveforms:


Notes:

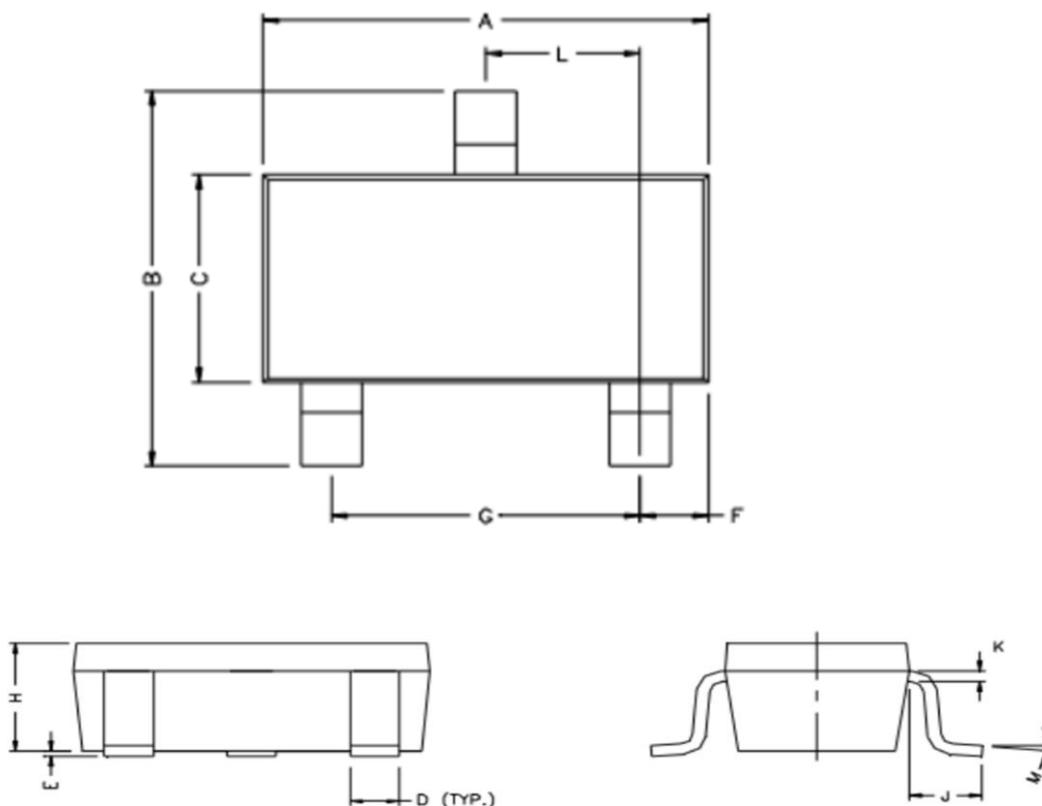
- ① Calculated continuous current based on maximum allowable junction temperature.
- ② Repetitive rating; pulse width limited by max. junction temperature.
- ③ The power dissipation PD is based on max. junction temperature, using junction-to-case thermal resistance.
- ④ The value of $R_{\theta JA}$ is measured with the device mounted on 1 in 2 FR-4 board with 2oz. Copper, in a still air environment with $T_A = 25^\circ\text{C}$

Typical Electrical and Thermal Characteristics


Figure1. Typical Output Characteristics

Figure2. Gate to Source Cut-off

Figure3. Drain-to-Source Breakdown Voltage vs. Junction Temperature

Figure4. $R_{DS(on)}$ vs. Junction Temperature

Figure5. Drain Current vs. Case Temperature

Figure6. Capacitance

Mechanical Data:

SOT-23 Package Outline(Unit:mm)



REF.	Millimeter		REF.	Millimete	
	Min.	Max.		Min.	Max.
A	2.80	3.00	G	1.80	2.00
B	2.30	2.50	H	0.90	1.1
C	1.20	1.40	K	0.10	0.20
D	0.30	0.50	J	0.35	0.70
E	0	0.10	L	0.92	0.98
F	0.45	0.55	M	0°	10°

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